# 2SC5954

## Silicon NPN triple diffusion planar type

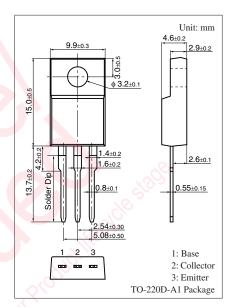
For power amplification with high forward current transfer ratio

#### ■ Features

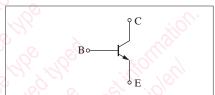
- High forward current transfer ratio h<sub>FE</sub> which has satisfactory linearity.
- ullet Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Full-pack package which can be installed to the heat sink with one screw.

### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	$V_{CBO}$	80	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	60	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	6	V	
Collector current	$I_{C}$	3	A	
Peak collector current	$I_{CP}$	6	A	
Collector power dissipation	P <sub>C</sub>	25	W	
$T_a = 25$ °C		2.0		
Junction temperature	T <sub>j</sub>	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C	



#### Internal Connection



### ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	$V_{CEO}$	$I_C = 10 \text{ mA}, I_B = 0$	60			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 80 \text{ V}, I_{E} = 0$			100	μΑ
Collector-emitter cutoff current (Base open)	$I_{CEO}$	$V_{CE} = 40 \text{ V}, I_{B} = 0$			100	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 6 \text{ V}, I_C = 0$			100	μΑ
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = 4 \text{ V}, I_{C} = 0.5 \text{ A}$	500		2300	_
M.S.	h <sub>FE2</sub>	$V_{CE} = 4 \text{ V}, I_{C} = 3 \text{ A}$	100			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 1 \text{ A}, I_B = 20 \text{ mA}$			0.6	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.1 \text{ A}, f = 10 \text{ MHz}$		200		MHz
Turn-on time	t <sub>on</sub>	$I_C = 1$ A, Resistance loaded		0.2		μs
Storage time	t <sub>stg</sub>	$I_{B1} = 0.1 \text{ A}, I_{B2} = -0.1 \text{ A}$		1.5		μs
Fall time	$t_{\rm f}$	$V_{CC} = 50 \text{ V}$		0.1		μs

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

#### 2. \*: Rank classification

Rank	Q	Р
h <sub>FE1</sub>	500 to 1500	1 300 to 2 300

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